

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A semiconductor device, comprising:
~~data lines over which data are transferred; and~~
~~a drive circuit for driving said data lines in a plurality of operating modes,~~
~~said plurality of operating modes including a dynamic operation mode in which said data~~
~~lines are precharged prior to transfer of the data over said data lines, and including a~~
~~static operation mode in which said data lines are not precharged prior to transfer of the~~
~~data over said data lines,~~

~~wherein said drive circuit drives said data lines in both said dynamic~~
~~operation mode and said static operation mode based on a control signal~~ a data supply
circuit configured to supply two signals that are complementary with each other to
represent a single value in a first operation mode and capable of assuming either
different signal levels or an identical signal level in a second operation mode;

a first data line;

a second data line; and

a drive circuit configured to set, in the first operation mode, the first data
line to a signal level responsive to said single value represented by the two
complementary signals, and configured to set, in the second operation mode, the first
data line to a signal level responsive to one of the two signals and the second data line
to a signal level responsive to another one of the two signals after precharging the first
and second data lines.
2. (Currently amended) The semiconductor device as claimed in claim 1,
further comprising a memory cell array to which said ~~data lines~~ first data line and said

second data line are connected, data read from the memory cell array being transferred over ~~said data lines~~ first data line and said second data line.

3. (Currently amended) The semiconductor device as claimed in claim 1, further comprising a test-dedicated line and ~~said data lines~~ first data line and said second data line.

4. (Currently amended) The semiconductor device as claimed in claim 3, further comprising a test result output circuit receiving said data lines at inputs thereof and outputting a test result, said test result and a logic level of said test-dedicated line forming a result of said predetermined test.

5. (Currently amended) The semiconductor device as claimed in claim 3, further comprising a precharge circuit precharging said ~~data lines~~ first data line, said second data line and said test-dedicated line.

6. (Currently amended) The semiconductor device as claimed in claim 5, said precharge circuit precharging said ~~data lines~~ first data line, said second data line and said test-dedicated line in said ~~dynamic~~ first operation mode only.

7. (Withdrawn) A semiconductor device comprising:
signal lines over which signals are transferred; and
a circuit precharging the signal lines and then driving the signal lines on

the basis of signals to be transferred in a first operation mode, and driving the signal lines on the basis of signals to be transferred in the absence of precharging in a second mode.

8. (Withdrawn) The semiconductor device as claimed in claim 7, further comprising a memory cell array to which the signal lines are connected, data read from the memory cell array being transferred over the signal lines.

9. (Withdrawn) The semiconductor device as claimed in claim 7, further comprising a test-dedicated line,

A predetermined test of the semiconductor device being performed using the test-dedicated line and the signal lines.

10. (Withdrawn) A semiconductor device comprising:
a signal line over which a signal is transferred;
first and second transistors respectively driving the signal line to a high level and a low level, respectively; and
a drive circuit controlling said first and second transistors to drive the signal line in first and second operating modes on the basis of a level of the signal to be transferred over the signal line, at least one of said first and second transistors further serving for precharging of the signal line,
the first operating mode needing precharging of the signal line and the second operating mode needing no precharging thereof.

11. (Withdrawn) A semiconductor device comprising:
signal lines over which signals are transferred;
first transistors respectively driving the signal lines to a high level;
second transistors respectively driving the signal lines to a low level; and
a circuit causing the second and first transistors to drive the signal lines
precharged to the high and low levels in advance to the low and high levels in a first
operating mode when the signals transferred are low and high, respectively, and
causing the first and second transistors to the high and low levels on the basis of
whether the signals transferred are high or low in a second operating mode.

12. (Withdrawn) The semiconductor device as claimed in claim 11, further
comprising third transistors precharging the signal lines in the first operating mode in
which the first and second transistors are OFF.

13. (Withdrawn) A semiconductor device comprising:
an internal circuit from which data items are supplied;
first signal lines over which signals corresponding to the data items are
transferred;
a second signal line;
a drive circuit driving the first signal lines based on the data items and
driving the second signal line based on the data items and a control signal; and a
precharge circuit precharging the first and second signal lines in a given operating
mode.

14. (Withdrawn) The semiconductor device as claimed in claim 13, further comprising a logic circuit making a given logical operation on the signals on the first signal lines.

15. (Withdrawn) The semiconductor device as claimed in claim 13, wherein the given operating mode is a test mode.

16. (Withdrawn) The semiconductor device as claimed in claim 13, wherein the internal circuit comprises a memory cell array.

17. (Withdrawn) A semiconductor device comprising:
an internal circuit from which data items are supplied;
first signal lines over which signals corresponding to the data items are transferred;
a second signal line;
a drive circuit driving the first signal lines based on the data items and driving the second signal line based on the data items and a control signal; and
a precharge circuit precharging the second signal line in a given operating mode.

18. (Withdrawn) The semiconductor device as claimed in claim 17, wherein the drive circuit comprises transistors driving the first signal lines based on the data

items, the transistors also precharging the first signal lines in the given operating mode.

19. (Withdrawn) The semiconductor device as claimed in claim 17, wherein the drive circuit comprises a logic circuit controlling the transistors on the basis of the data items and a control signal designating the given operating mode.

20. (Withdrawn) The semiconductor device as claimed in claim 17, wherein the internal circuit comprises a memory cell array.